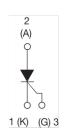


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High Voltage, Phase Control Thyristor, 12 A

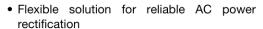


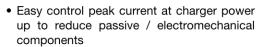


PRIMARY CHARACTERISTICS					
I _{T(AV)}	8 A				
V _{DRM} /V _{RRM}	800 V				
V _{TM}	1.2 V				
I _{GT}	15 mA				
T _J	-40 to +125 °C				
Package	TO-220AB				
Circuit configuration	Single SCR				

FEATURES

- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test





 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

- · On-board and off-board EV / HEV battery chargers
- · Renewable energy inverters

DESCRIPTION

The VS-12TTS08HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А			

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	8	A		
I _{T(RMS)}		12.5			
V _{RRM} /V _{DRM}		800	V		
I _{TSM}		110	A		
V _T	8 A, T _J = 25 °C	1.2	V		
dV/dt		150	V/µs		
dl/dt		100	A/µs		
T _J	Range	-40 to +125	°C		

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} / I _{DRM} AT 125 °C mA				
VS-12TTS08HM3	800	800	5.0				



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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum average on-state current	I _{T(AV)}	T = 100 °C 100° conduction half airc ways	8	- A	
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 180° conduction, half sine wave	12.5		
Maximum peak one-cycle	I	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	95	A	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T _J = 125 °C	110		
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s	
Maximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied, T _J = 125 °C	64		
Maximum I ² √t for fusing	I²√t	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C	640	A²√s	
Maximum on-state voltage drop	V_{TM}	8 A, T _J = 25 °C	1.2	V	
On-state slope resistance	r _t	T, _I = 125 °C	16.2	mΩ	
Threshold voltage	V _{T(TO)}	11 - 123 0	0.87	V	
Maximum reverse and direct leakage current	l=/l=	$T_J = 25 ^{\circ}\text{C}$ $V_B = \text{rated } V_{BBM} / V_{DBM}$	0.05		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_J = 125 ^{\circ}\text{C}$	5.0		
Typical holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	30	mA	
Typical latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C	50		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = \text{open}$	150	V/µs	
Maximum rate of rise of turned-on current	dl/dt		100	A/µs	

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	VV		
Maximum peak positive gate current	+I _{GM}		1.5	Α		
Maximum peak negative gate voltage	-V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	20			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	15	mA		
		Anode supply = 6 V, resistive load, T _J = 125 °C	10			
		Anode supply = 6 V, resistive load, T _J = -65 °C	1.2			
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	1	v		
		Anode supply = 6 V, resistive load, T _J = 125 °C	0.7	V		
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = reted value	0.2			
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = rated value	0.1	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8			
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	3	μs		
Typical turn-off time	tq	1J = 120 O	100			



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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5			
Maximum thermal resistance, junction to ambient	R _{thJA}		62	°C/W		
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, and greased	0.5			
Approximate weight			2	g		
Approximate weight			0.07	oz.		
Mounting torque	minimum		6 (5)	kgf · cm		
	maximum		12 (10)	(lbf · in)		
Marking device		Case style TO-220AB	12TT	S08H		

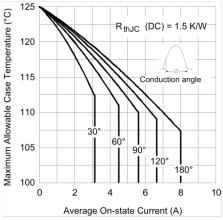


Fig. 1 - Current Rating Characteristics

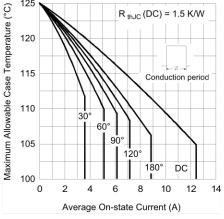


Fig. 2 - Current Rating Characteristics

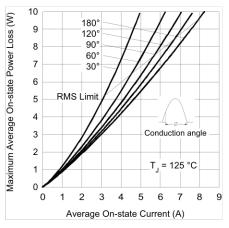


Fig. 3 - On-State Power Loss Characteristics

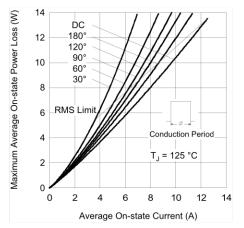


Fig. 4 - On-State Power Loss Characteristics

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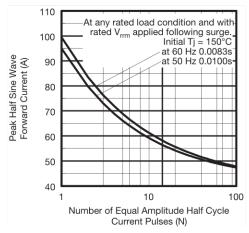


Fig. 5 - Maximum Non-Repetitive Surge Current

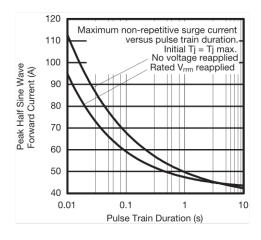


Fig. 6 - Maximum Non-Repetitive Surge Current

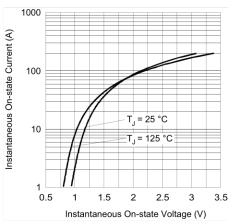


Fig. 7 - On-State Voltage Drop Characteristics

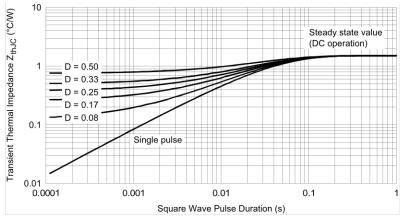
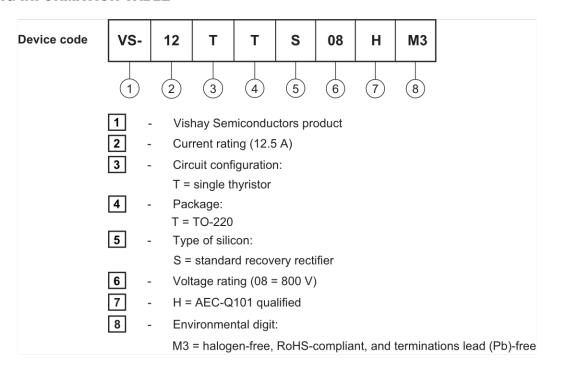


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-12TTS08HM3	50	1000	Antistatic plastic tube			

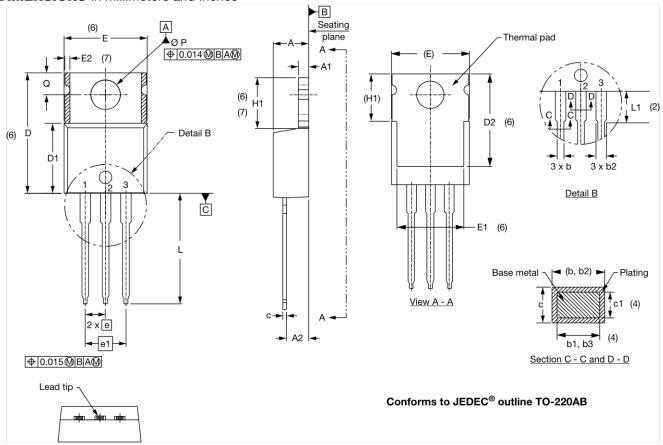
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95222</u>				
Part marking information	www.vishay.com/doc?95028			



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TO-220AB





SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	5.84	6.86	0.230	0.270	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC® TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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